

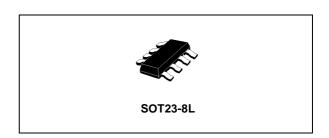
## 74V2G384

### **DUAL HIGH SPEED BUS SWITCH**

- HIGH SPEED:  $t_{PD} = 0.5$ ns (TYP.) at  $V_{CC} = 5V$
- LOW POWER DISSIPATION:  $I_{CC} = 1\mu A(MAX.)$  at  $T_A = 25$ °C
- LOW "ON" RESISTANCE at  $V_{CC}$ =5.0V:  $R_{ON}$ =  $7\Omega$  (TYP),  $V_{IN}$ =0V,  $I_{I/O}$ =30mA  $R_{ON}$ =  $20\Omega$  (TYP),  $V_{IN}$ =2.4V,  $I_{I/O}$ =10mA
- OPERATING VOLATGE RANGE: V<sub>CC</sub> (OPR.) = 3.0V TO 5.5V
- 5V TOLERANT ON CONTROL PIN
- HIGH NOISE IMMUNITY: V<sub>NIH</sub> = V<sub>NIL</sub> = 28% V<sub>CC</sub> (MIN.)



The 74V2G384 is an advanced high-speed CMOS DUAL HIGH SPEED BUS SWITCH fabricated in silicon gate  $C^2$ MOS technology. It's designed to operate from 3V to 5.5V, making this device ideal for portable applications. It's offers  $7\Omega$  Resistance typical value at  $V_{CC}$ =4.5V. Additional key feature



#### **ORDER CODES**

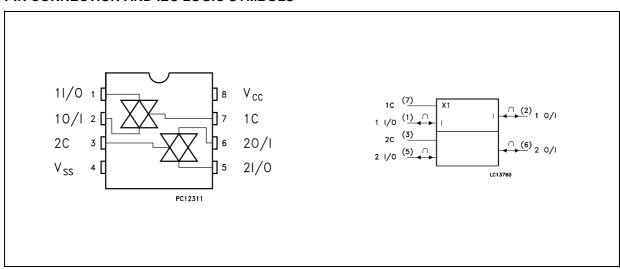
PACKAGE	T&R
SOT23-8L	74V2G384STR

are fast switching speed ( $t_{ON}$ =3.8ns,  $t_{OFF}$ =3.3ns Typical) and Low Power Consumption.

The OE input is provided to control the switch; the switch is ON when the OE input is held low and OFF when OE is held high.

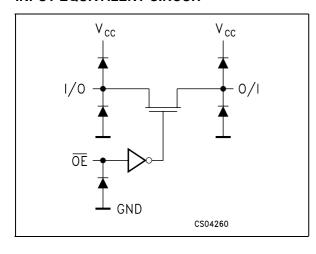
It's available in the commercial and extended temperature range in SOT23-8L package.

#### PIN CONNECTION AND IEC LOGIC SYMBOLS



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### **INPUT EQUIVALENT CIRCUIT**



#### **PIN DESCRIPTION**

PIN No	SYMBOL	NAME AND FUNCTION
1, 5	11/0, 21/0	Independent Input/Output
2, 6	10/I, 20/I	Independent Output/Input
7, 3	10E, 20E	Enable Input (Active HIGH)
4	GND	Ground (0V)
8	V <sub>CC</sub>	Positive Supply Voltage

#### **TRUTH TABLE**

ŌĒ	SWITCH FUNCTION
L	ON
Н	OFF *

<sup>\*</sup> High Impedance State

### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7.0	V
VI	DC Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>IC</sub>	DC Control Input Voltage	-0.5 to +7.0	V
Vo	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	± 20	mA
I <sub>IK</sub>	DC Control Input Diode Current	- 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
Io	DC Output Current	± 50	mA
$I_{CC}$ or $I_{GND}$	DC V <sub>CC</sub> or Ground Current	± 50	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	3 to 5.5	V
V <sub>I</sub>	Input Voltage	0 to V <sub>CC</sub>	V
V <sub>IC</sub>	Control Input Voltage	0 to 5.5	V
V <sub>O</sub>	Output Voltage	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 1) V <sub>CC</sub> = 5.0V	0 to 20	ns/V

<sup>1)</sup> V<sub>IN</sub> from 30% to 70% of V<sub>CC</sub> on control pin

### **DC SPECIFICATIONS**

		Т	Test Condition		Value						
Symbol	ol Parameter		neter V <sub>CC</sub>		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C	
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V <sub>IH</sub>	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	3.0 to 5.5		0.7V <sub>CC</sub>			0.7V <sub>CC</sub>		0.7V <sub>CC</sub>		V
V <sub>IL</sub>	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	3.0 to 5.5				0.3V <sub>CC</sub>		0.3V <sub>CC</sub>		0.3V <sub>CC</sub>	V
R <sub>ON</sub>	ON Resistance	3.0	$V_{IC} = V_{IL}$ $V_{I/O} = GND$ $I_{I/O} \le 30 \text{ mA}$		9			13		20	Ω
		4.5	$V_{IC} = V_{IL}$ $V_{I/O} = GND$ $I_{I/O} \le 30 \text{ mA}$		7			10		15	Ω
R <sub>ON</sub>	ON Resistance	3.0	$V_{IC} = V_{IL}$ $V_{I/O} = 1.5V$ $I_{I/O} \le 10 \text{ mA}$		32			60		80	Ω
		4.5	$V_{IC} = V_{IL}$ $V_{I/O} = 2.4V$ $I_{I/O} \le 10 \text{ mA}$		20			40		60	Ω
l <sub>OFF</sub>	Input/Output Leakage Current (SWITCH OFF)	5.5	$V_{OS} = V_{CC}$ to GND $V_{IS} = V_{CC}$ to GND $V_{IC} = V_{IH}$			±0.1		± 1		± 10	μΑ
I <sub>IN</sub>	Control Input Leakage Current	0 to 5.5	V <sub>IC</sub> = 5.5V or GND			± 0.1		± 1.0		± 1.0	μА
I <sub>CC</sub>	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			1		10		20	μА

# AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 pF$ , Input $t_r = t_f = 3 ns$ )

		Т	est Condition	Value							
Symbol	Parameter	v <sub>cc</sub>		Т	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t <sub>PD</sub>	Delay Time	3.3(*)	$t_r = t_f = 6ns$		0.8	1.2		1.5		2.0	no
		5.0 <sup>(**)</sup>	$t_r = t_f = 6ns$		0.5	0.8		1.0		1.5	ns
t <sub>PLZ</sub> t <sub>PHZ</sub>	Output Disable Time	3.3 <sup>(*)</sup>	$R_1 = 500\Omega$ $V_{IN} = 1.5V$		8.5	12.0		14.0		16.0	ns
		5.0 <sup>(**)</sup>	$R_1 = 500 \Omega$ $V_{IN}=2.4V$		3.8	6.5		9.0		10.0	
t <sub>PZL</sub>	Output Enable	3.3 <sup>(*)</sup>	$R_1 = 1K\Omega$ $V_{IN}=1.5V$		7.3	12.0		14.0		16.0	ne
t <sub>PZH</sub>	Time	5.0 <sup>(**)</sup>	$R_1 = 1K\Omega$ $V_{IN}=2.4V$		3.3	5.0		7.5		8.5	ns

<sup>(\*)</sup> Voltage range is  $3.3V \pm 0.3V$  (\*\*) Voltage range is  $5.0V \pm 0.5V$ 

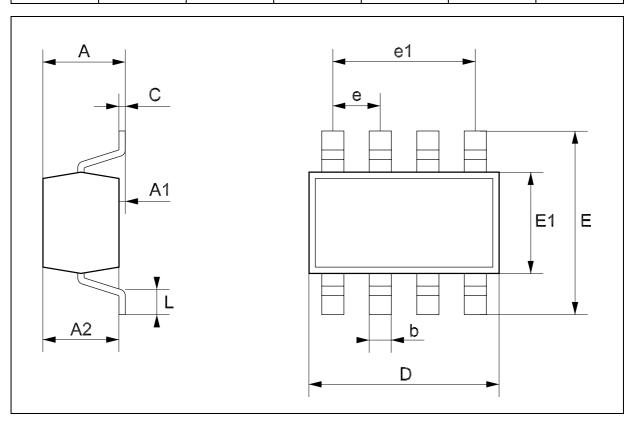
#### **CAPACITIVE CHARACTERISTICS**

		1	est Condition	Value							
Symbol Parameter	v <sub>cc</sub>	Vcc		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C <sub>IN</sub>	Input Capacitance				4	10		10		10	pF
C <sub>I/O</sub>	Output Capacitance				7						pF
C <sub>PD</sub>	Power Dissipation	3.3			2.5						
	Capacitance (note 1)	5.0			3						pF

<sup>1)</sup> C<sub>PD</sub> is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I<sub>CC(opr)</sub> = C<sub>PD</sub> x V<sub>CC</sub> x f<sub>IN</sub> + I<sub>CC</sub>

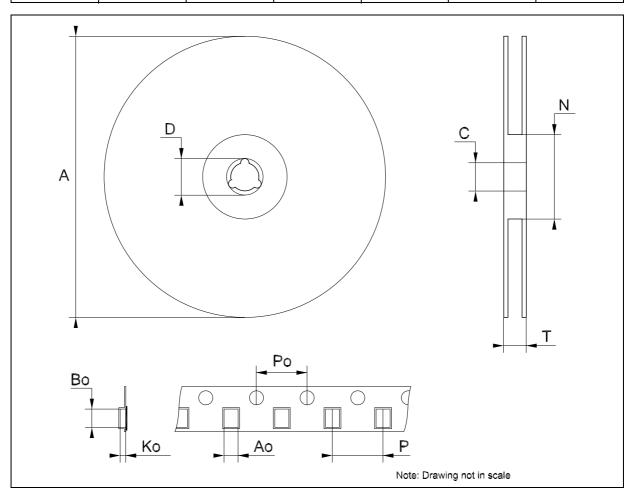
## **SOT23-8L MECHANICAL DATA**

DIM		mm.		mils				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А	0.90		1.45	35.4		57.1		
A1	0.00		0.15	0.0		5.9		
A2	0.90		1.30	35.4		51.2		
b	0.22		0.38	8.6		14.9		
С	0.09		0.20	3.5		7.8		
D	2.80		3.00	110.2		118.1		
E	2.60		3.00	102.3		118.1		
E1	1.50		1.75	59.0		68.8		
е	0	.65			25.6			
e1		1.95			76.7			
L	0.35		0.55	13.7		21.6		



# Tape & Reel SOT23-xL MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А			180			7.086		
С	12.8	13.0	13.2	0.504	0.512	0.519		
D	20.2			0.795				
N	60			2.362				
Т			14.4			0.567		
Ao	3.13	3.23	3.33	0.123	0.127	0.131		
Во	3.07	3.17	3.27	0.120	0.124	0.128		
Ko	1.27	1.37	1.47	0.050	0.054	0.0.58		
Po	3.9	4.0	4.1	0.153	0.157	0.161		
Р	3.9	4.0	4.1	0.153	0.157	0.161		



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